

Silicon Carbide (SiC) **Schottky Diode** - EliteSiC, 10 A, 1200 V, D1, TO-247-2L

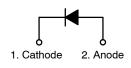
FFSH10120A-F155

Description

Silicon Carbide (SiC) Schottky Diodes use a completely new technology that provides superior switching performance and higher reliability compared to Silicon. No reverse recovery current, temperature independent switching characteristics, and excellent thermal performance sets Silicon Carbide as the next generation of power semiconductor. System benefits include highest efficiency, faster operating frequency, increased power density, reduced EMI, and reduced system size & cost.

Features

- Max Junction Temperature 175°C
- Avalanche Rated 100 mJ
- High Surge Current Capacity
- Positive Temperature Coefficient
- Ease of Paralleling
- No Reverse Recovery/No Forward Recovery
- No Reverse Recovery/No Forward Recovery
 These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant
 Applications
 General Purpose
 SMPS, Solar Inverter, UPS
 Power Switching Circuits
 See detail this data seems of the support of the supp

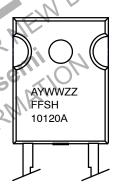


Schottky Diode



TO-247-2LD CASE 340DC

MARKING DIAGRAM



FFSH10120A

- = Assembly Plant Code
- = Date Code (Year & Week)
- = Lot Code
- = Specific Device Code

ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

ABSOLUTE MAXIMUM RATINGS ($T_C = 25^{\circ}C$ unless otherwise noted)

Symbol	Parameter	Value	Unit	
V _{RRM}	Peak Repetitive Reverse Voltage	1200	V	
E _{AS}	Single Pulse Avalanche Energy (Note 1)	100	mJ	
I _F	Continuous Rectified Forward Current @ T _C <	10	Α	
	Continuous Rectified Forward Current @ T _C <	135°C	17	
I _{F, Max}	Non-Repetitive Peak Forward Surge Current	titive Peak Forward Surge Current		Α
		T _C = 150°C, 10 μs	800	Α
I _{F,SM}	Non-Repetitive Forward Surge Current	Half-Sine Pulse, t _p = 8.3 ms	90	Α
I _{F,RM}	Repetitive Forward Surge Current	Half-Sine Pulse, t _p = 8.3 ms	35	Α
Ptot	Power Dissipation	T _C = 25°C	193	W
		T _C = 150°C	32	W
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +175	<i>7</i> 1 °C
	TO-247 Mounting Torque, M3 Screw	60	Ncm	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. E_{AS} of 100 mJ is based on starting T_J = 25°C, L = 0.5 mH, I_{AS} = 20 A, V = 50 V.

THERMAL CHARACTERISTICS

Symbol	Parameter	\$0,	Value	Unit
$R_{ heta JC}$	Thermal Resistance, Junction to Case, Max	CO, V	0.78	°C/W

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Symbol	Parameter	Test Condition	Min	Тур	Max	Unit
V _F	Forward Voltage	I _F = 10 A, T _C = 25°C	0R-11	1.45	1.75	V
		I _F = 10 A, T _C = 125°C	0'-	1.7	2.0	
		$I_F = 10 \text{ A}, T_C = 175^{\circ}\text{C}$	ı	2.0	2.4	
I _R	Reverse Current	$V_R = 1200 \text{ V}, T_C = 25^{\circ}\text{C}$	ı	ı	200	μΑ
		V _R = 1200 V, T _C = 125°C	ı	ı	300	
	MODLE	V _R = 1200 V, T _C = 175°C	ı	ı	400	
Q_C	Total Capacitive Charge	V = 800 V	ı	62	-	nC
С	Total Capacitance	V _R = 1 V, f = 100 kHz	_	612	_	pF
11		V _R = 400 V, f = 100 kHz	ı	58	-	
•		V _R = 800 V, f = 100 kHz	-	47	-	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

ORDERING INFORMATION

Part Number	Top Marking	Package	Shipping
FFSH10120A-F155	FFSH10120A	TO-247-2LD (Pb-Free / Halogen Free)	30 Units / Tube

TYPICAL CHARACTERISTICS

(T_J = 25°C UNLESS OTHERWISE NOTED)

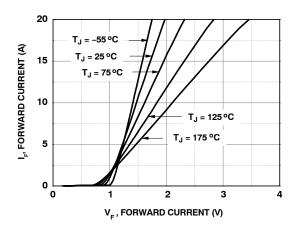


Figure 1. Forward Characteristics

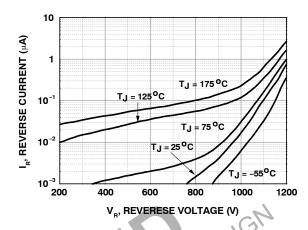


Figure 2. Reverse Characteristics

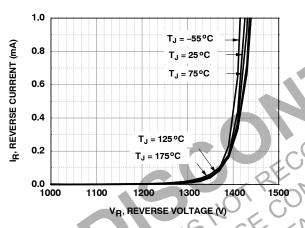


Figure 3. Reverse Characteristics

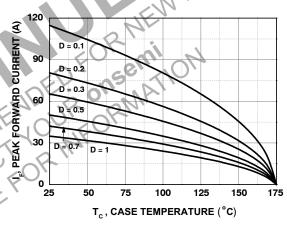


Figure 4. Current Derating

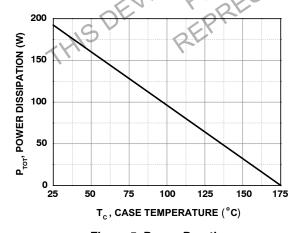


Figure 5. Power Derating

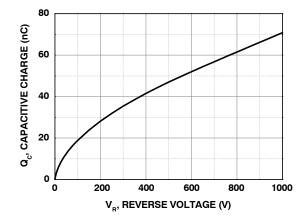
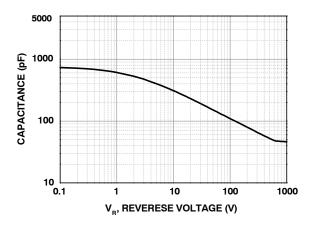


Figure 6. Capacitive Charge vs. Reverse Voltage

TYPICAL CHARACTERISTICS

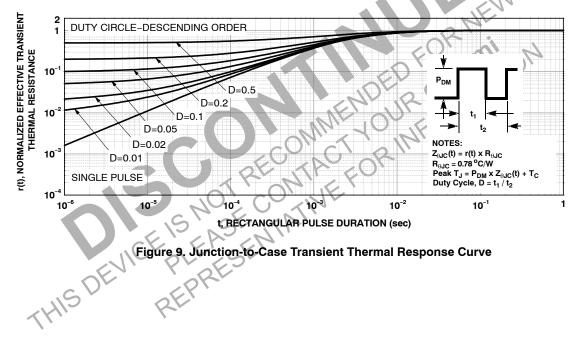
(T_J = 25°C UNLESS OTHERWISE NOTED)



30 E_c, CAPACITIVE ENERGY (μJ) 20 10 0 400 600 800 1000 V_R, REVERVE VOLTAGE (V)

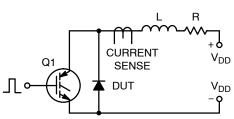
Figure 7. Capacitance vs. Reverse Voltage

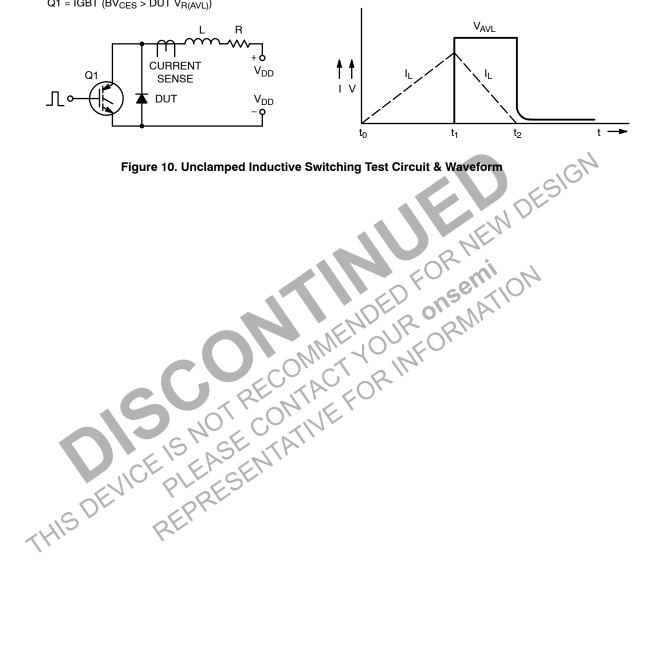
Figure 8. Capacitance Stored Energy



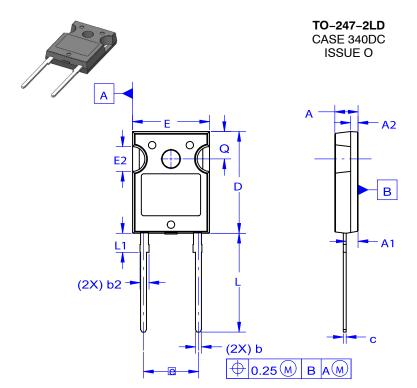
TEST CIRCUIT AND WAVEFORMS

L = 0.5 mH $R < 0.1 \Omega$ $V_{DD} = 50 \text{ V}$
$$\begin{split} &\mathsf{EAVL} = 1/2\mathsf{L}12 \left[\mathsf{V}_{\mathsf{R}(\mathsf{AVL})} \ / \ (\mathsf{V}_{\mathsf{R}(\mathsf{AVL})} - \mathsf{V}_{\mathsf{DD}}) \right] \\ &\mathsf{Q1} = \mathsf{IGBT} \ (\mathsf{BV}_{\mathsf{CES}} > \mathsf{DUT} \ \mathsf{V}_{\mathsf{R}(\mathsf{AVL})}) \end{split}$$

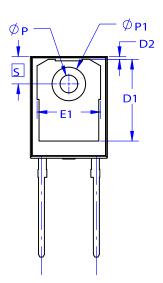








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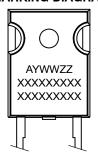


NOTES:

- A. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR PROTRUSIONS.
- B. ALL DIMENSIONS ARE IN MILLIMETERS.
- C. DIMENSION AND TOLERANCE AS PER ASME Y14.5-2009.
- D. DIMENSION A1 TO BE MEASURED IN THE REGION DEFINED BY L1.
- E. LEAD FINISH IS UNCONTROLLED IN THE REGION DEFINED BY L1.

DIM	MILLIMITERS				
DIM	MIN	NOM	MAX		
Α	4.58	4.70	4.82		
A 1	2.20	2.40	2.60		
A2	1.40	1.50	1.60		
b	1.17	1.26	1.35		
b2	1.60	1.72	1.84		
С	0.51	0.61	0.71		
D	20.32	20.57	20.82		
D1	13.08	~	~		
D2	0.51	0.93	1.35		
Е	15.37	15.62	15.87		
E1	12.81	~	~		
E2	4.96	5.08	5.20		
е	~	11.12	~		
L	19.75	20.00	20.25		
L1	3.69	3.81	3.93		
ØР	3.51	3.58	3.65		
Ø P 1	6.60	6.80	7.00		
Q	5.34	5.46	5.58		
S	5.34	5.46	5.58		

GENERIC MARKING DIAGRAM*



XXXXX = Specific Device Code

A = Assembly Location
Y = Year

WW = Work Week
ZZ = Assembly Lot Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb—Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

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DESCRIPTION:	TO-247-2LD		PAGE 1 OF 1

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